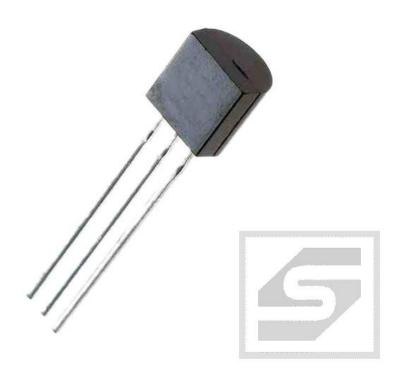


Tyrystor MCR22-6;TO92;1.5A;400V; ON-Semiconductor;RoHS



Dane techniczne:

Nazwa: MCR22-6

Typ: Tyrystor

Napięcie wsteczne: 400V Prąd przewodzenia: 1.5A

Prąd bramki: 30µA Obudowa: TO92

Producent: ON-Semiconductor

Preferred Device

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed and tested for repetitive peak operation required for CD ignition, fuel ignitors, flash circuits, motor controls and low-power switching applications.

- 150 Amperes for 2 µs Safe Area
- High dv/dt
- Very Low Forward "On" Voltage at High Current
- Low-Cost TO-226AA (TO-92)
- Device Marking: Device Type, e.g., MCR22-6, Date Code
- These devices are available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at www.onsemi.com for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage $(R_{GK} = IK, T_J = -40 \text{ to } +110^{\circ}\text{C}, \\ \text{Sine Wave, 50 to 60 Hz, Gate Open)} \\ \text{MCR22-6} \\ \text{MCR22-8}$	V _{DRM,} V _{RRM}	400 600	Volts
On-State Current RMS (180° Conduction Angles, T _C = 80°C)	I _{T(RMS)}	1.5	Amps
Peak Non-repetitive Surge Current, T _A = 25°C (1/2 Cycle, Sine Wave, 60 Hz)	I _{TSM}	15	Amps
Circuit Fusing Considerations (t = 8.3 ms)	I ² t	0.9	A ² s
Forward Peak Gate Power (Pulse Width ≤ 1.0 μsec, T _A = 25°C)	P _{GM}	0.5	Watt
Forward Average Gate Power (t = 8.3 msec, T _A = 25°C)	$P_{G(AV)}$	0.1	Watt
Forward Peak Gate Current (Pulse Width ≤ 1.0 μs, T _A = 25°C)	I _{FGM}	0.2	Amp
Reverse Peak Gate Voltage (Pulse Width ≤ 1.0 μs, T _A = 25°C)	V_{RGM}	5.0	Volts
Operating Junction Temperature Range @ Rated V _{RRM} and V _{DRM}	TJ	–40 to +110	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



ON Semiconductor

http://onsemi.com

SCRs 1.5 AMPERES RMS 400 thru 600 VOLTS





TO-92 (TO-226AA) CASE 029 STYLE 10

PIN ASSIGNMENT			
1	Cathode		
2	Gate		
3	Anode		

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	160	°C/W
Lead Solder Temperature (Lead Length ≥ 1/16" from case, 10 s Max)	T _L	+260	°C

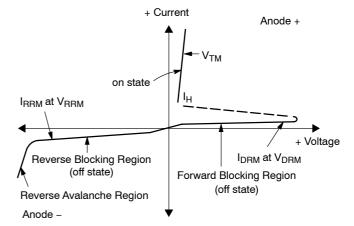
ELECTRICAL CHARACTERISTICS (To = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS					•	
Peak Repetitive Forward or Reverse Blocking Current (V_{AK} = Rated V_{DRM} or V_{RRM} ; R_{GK} = 1000 Ohms)	T _C = 25°C T _C = 110°C	I _{DRM} , I _{RRM}		_ _	10 200	μ Α μ Α
ON CHARACTERISTICS						
Peak Forward On-State Voltage ⁽¹⁾ (I _{TM} = 1 A Peak)		V _{TM}	_	1.2	1.7	Volts
Gate Trigger Current (Continuous dc) ⁽²⁾ (V _{AK} = 6 Vdc, R _L = 100 Ohms)	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	I _{GT}	_	30 —	200 500	μА
Gate Trigger Voltage (Continuous dc) ⁽²⁾ (V _{AK} = 7 Vdc, R _L = 100 Ohms)	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	V _{GT}	_	_	0.8 1.2	Volts
Gate Non-Trigger Voltage ⁽¹⁾ (V _{AK} = 12 Vdc, R _L = 100 Ohms)	T _C = 110°C	V_{GD}	0.1	_	_	Volts
		l _H	<u> </u>	2.0 —	5.0 10	mA
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off–State Voltage (T _C = 110°C)		dv/dt	_	25	_	V/μs

⁽¹⁾ Pulse Width = 1.0 ms, Duty Cycle ≤ 1%.(2) R_{GK} Current not included in measurement.

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak on State Voltage
I _H	Holding Current



CURRENT DERATING

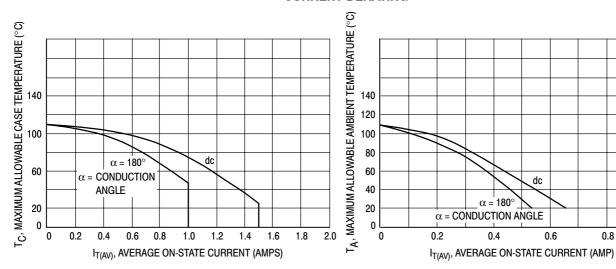


Figure 1. Maximum Case Temperature

Figure 2. Maximum Ambient Temperature

1.0

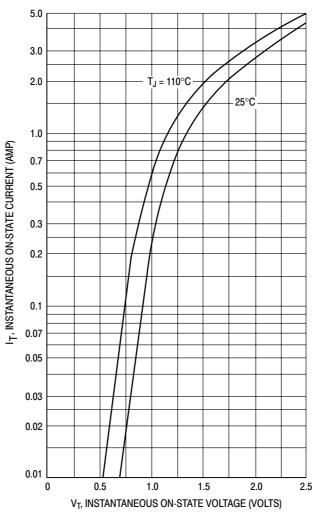


Figure 3. Typical Forward Voltage

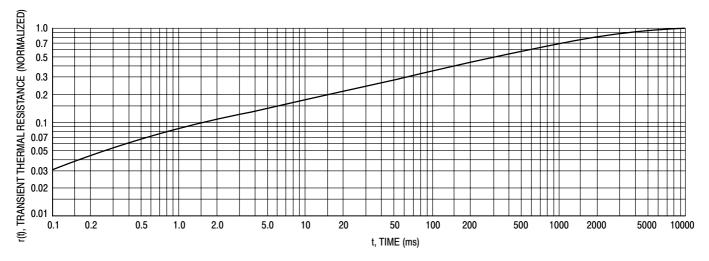


Figure 4. Thermal Response

TYPICAL CHARACTERISTICS

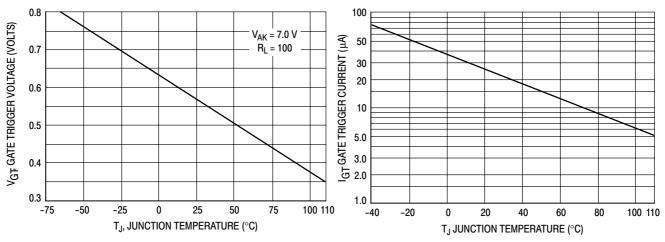


Figure 5. Typical Gate Trigger Voltage

Figure 6. Typical Gate Trigger Current

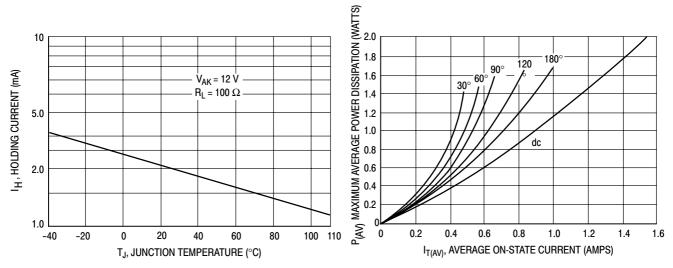


Figure 7. Typical Holding Current

Figure 8. Power Dissipation

TO-92 EIA RADIAL TAPE IN FAN FOLD BOX OR ON REEL

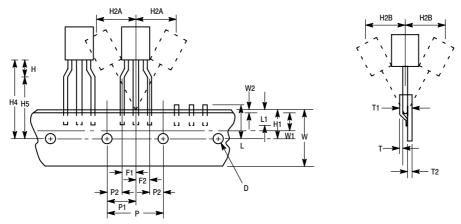


Figure 9. Device Positioning on Tape

			Specification		
		Inc	hes	Millir	neter
Symbol	Item	Min	Max	Min	Max
D	Tape Feedhole Diameter	0.1496	0.1653	3.8	4.2
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8
Н	Bottom of Component to Seating Plane	.059	.156	1.5	4.0
H1	Feedhole Location	0.3346	0.3741	8.5	9.5
H2A	Deflection Left or Right	0	0.039	0	1.0
H2B	Deflection Front or Rear	0	0.051	0	1.0
H4	Feedhole to Bottom of Component	0.7086	0.768	18	19.5
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5
L	Defective Unit Clipped Dimension	0.3346	0.433	8.5	11
L1	Lead Wire Enclosure	0.09842	_	2.5	_
Р	Feedhole Pitch	0.4921	0.5079	12.5	12.9
P1	Feedhole Center to Center Lead	0.2342	0.2658	5.95	6.75
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95
Т	Adhesive Tape Thickness	0.06	0.08	0.15	0.20
T1	Overall Taped Package Thickness	_	0.0567	_	1.44
T2	Carrier Strip Thickness	0.014	0.027	0.35	0.65
W	Carrier Strip Width	0.6889	0.7481	17.5	19
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3
W2	Adhesive Tape Position	.0059	0.01968	.15	0.5

NOTES:

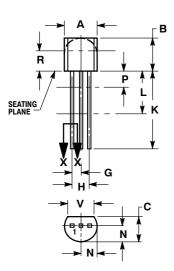
- 1. Maximum alignment deviation between leads not to be greater than 0.2 mm.
- 2. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.
- 3. Component lead to tape adhesion must meet the pull test requirements.
- 4. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
- 5. Holddown tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
- 6. No more than 1 consecutive missing component is permitted.
- 7. A tape trailer and leader, having at least three feed holes is required before the first and after the last component.
- 8. Splices will not interfere with the sprocket feed holes.

ORDERING & SHIPPING INFORMATION: MCR22 Series packaging options, Device Suffix

U.S.	Europe Equivalent	Shipping	Description of TO92 Tape Orientation
MCR22-6,8 MCR22-6RLRA MCR22-6RLRP	MCR22-8RL1 MCR22-8ZL1	Radial Tape and Reel (2K/Reel) Bulk in Box (5K/Box) Radial Tape and Reel (2K/Reel) Radial Tape and Fan Fold Box (2K/Box) Radial Tape and Fan Fold Box (2K/Box)	Flat side of TO92 and adhesive tape visible N/A, Bulk Round side of TO92 and adhesive tape visible Round side of TO92 and adhesive tape visible Flat side of TO92 and adhesive tape visible

PACKAGE DIMENSIONS

TO-92 (TO-226AA) CASE 029-11 **ISSUE AJ**





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 10:

PIN 1. CATHODE

2. GATE

3. ANODE

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and war engineer trademarks of semiconductor components industries, Ite (SciLLC) solitate services are injective to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082-1312 USA Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative